

TRANSMITTAL FORM

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|---------------------------|----------------------|
| Application Serial Number | 10/022,689 |
| Filing Date | December 17, 2001 |
| First Named Inventor | Fitzgerald |
| Group Art Unit | 2813 |
| Examiner Name | Laura M. Schillinger |
| Attorney Docket No. | ASC-023DVC2 |
| Patent No. | Not applicable |
| Issue Date | Not applicable |

ENCLOSURES (check all that apply)

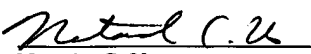
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| <input checked="" type="checkbox"/> Fee Transmittal Form <input checked="" type="checkbox"/> Check Attached <input type="checkbox"/> Copy of Fee Transmittal Form | <input type="checkbox"/> Copy of Notice to File Missing Parts of Application <input type="checkbox"/> Formal Drawing(s) | <input type="checkbox"/> Notice of Appeal to Board of Patent Appeals and Interferences <input type="checkbox"/> Appeal Brief (in triplicate) |
| <input type="checkbox"/> Amendment/Response <input type="checkbox"/> Preliminary <input type="checkbox"/> After Final <input type="checkbox"/> Affidavits/declaration(s) <input type="checkbox"/> Letter to Official Draftsperson including Drawings [Total Sheets ____] | <input type="checkbox"/> Request For Continued Examination (RCE) Transmittal <input type="checkbox"/> Power of Attorney (Revocation of Prior Powers) <input type="checkbox"/> Terminal Disclaimer | <input type="checkbox"/> Status Inquiry <input checked="" type="checkbox"/> Return Receipt Postcard <input checked="" type="checkbox"/> Certificate of First Class Mailing under 37 C.F.R. 1.8 <input type="checkbox"/> Certificate of Facsimile Transmission under 37 C.F.R. 1.8 |
| <input type="checkbox"/> Petition for Extension of Time | <input type="checkbox"/> Executed Declaration and Power of Attorney for Utility or Design Patent Application | <input type="checkbox"/> Additional Enclosure(s) (please identify below) |
| <input checked="" type="checkbox"/> Supplemental Information Disclosure Statement <input checked="" type="checkbox"/> Form PTO-1449 <input checked="" type="checkbox"/> Copies of IDS Citations | <input type="checkbox"/> Small Entity Statement <input type="checkbox"/> CD(s) for large table or computer program | |
| <input type="checkbox"/> Certified Copy of Priority Document(s) | <input type="checkbox"/> Amendment After Allowance | |
| <input type="checkbox"/> Sequence Listing submission <input type="checkbox"/> Paper Copy/CD <input type="checkbox"/> Computer Readable Copy <input type="checkbox"/> Statement verifying identity of above | <input type="checkbox"/> Request for Certificate of Correction <input type="checkbox"/> Certificate of Correction (in duplicate) | |

CORRESPONDENCE ADDRESS

Direct all correspondence to: Patent Administrator
Testa, Hurwitz & Thibault, LLP
High Street Tower
125 High Street
Boston, MA 02110
Tel. No.: (617) 248-7000
Fax No.: (617) 248-7100

SIGNATURE BLOCK

Respectfully submitted,

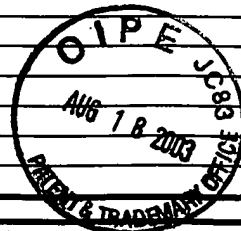

Natasha C. Us
Attorney for the Applicant
Testa, Hurwitz & Thibault, LLP
High Street Tower
125 High Street
Boston, MA 02110

Date: August 13, 2003
Reg. No. 44,381
Tel. No.: (617) 310-8327
Fax No.: (617) 248-7100

FEE TRANSMITTAL FY 2003

Complete if Known

| | |
|---------------------------|----------------------|
| Application Serial Number | 10/022,689 |
| Filing Date | December 17, 2001 |
| First Named Inventor | Fitzgerald |
| Group Art Unit | 2813 |
| Examiner Name | Laura M. Schillinger |
| Attorney Docket No. | ASC-023DVC2 |



METHOD OF PAYMENT

1. ☒ Payment Enclosed:
☒ Check ☐ Money Order ☐ Other
2. ☒ The Commissioner is hereby authorized to credit or charge any fee indicated below for this submission to Deposit Account No. 20-0531.
☐ Required Fees (copy of this sheet enclosed).
☒ Additional fee required under 37 CFR 1.16 and 1.17.
☒ Overpayment Credit.
3. ☐ Applicant claims small entity status.

FEE CALCULATION

1. FILING FEE

Large Entity

| Fee (\$) | Fee Description | Fee Paid |
|----------|------------------------|----------|
| 750 | Utility filing fee | |
| 330 | Design filing fee | |
| 160 | Provisional filing fee | |

| Number Filed | Number Extra | Rate | Amount |
|--------------|--------------|------|--------|
|--------------|--------------|------|--------|

Total Claims - 20 = x \$ 18.00 =

Independent Claims - 3 = x \$ 84.00 =

☐ Multiple Dependent Claim(s), if any \$280.00 =

TOTAL:
SMALL ENTITY DISCOUNT:
SUBTOTAL (1) (\$) 0.00

2. AMENDMENT CLAIM FEES

| Claims Remaining After Amend. | Highest No. Previously Paid For | Present Extra | Rate | Fee Paid |
|-------------------------------|---------------------------------|---------------|------|----------|
|-------------------------------|---------------------------------|---------------|------|----------|

Total - = x \$ 18.00 =

Indep. - = x \$ 84.00 =

☐ First Presentation of Multiple Dep. Claim + \$280.00 =

TOTAL: (\$)
SMALL ENTITY DISCOUNT: (\$)
SUBTOTAL (2) (\$) 0.00

FEE CALCULATION (continued)

3. ADDITIONAL FEES

| Large Entity Fee (\$) | Small Entity Fee (\$) | Fee Description | Fee Paid |
|-----------------------|-----------------------|--|----------|
| 130 | 65 | Surcharge - late filing fee or oath | |
| 50 | 25 | Surcharge - late provisional filing fee or cover sheet | |
| 130 | 130 | Non-English specification | |
| 2,520 | 2,520 | Request for ex parte reexamination | |
| 110 | 55 | Extension for reply within first month | |
| 410 | 205 | Extension for reply within second month | |
| 930 | 465 | Extension for reply within third month | |
| 1450 | 725 | Extension for reply within fourth month | |
| 1970 | 985 | Extension for reply within fifth month | |
| 320 | 160 | Notice of Appeal | |
| 320 | 160 | Filing a brief in support of an appeal | |
| 280 | 140 | Request for oral hearing | |
| 130 | 130 | Petitions to the Commissioner | |
| 180 | 180 | Submission of Information Disclosure Statement | 180.00 |
| 750 | 375 | Filing a submission after final rejection (37 CFR 1.129(a)) | |
| 750 | 375 | For each additional invention to be examined (37 CFR 1.129(b)) | |
| 100 | 100 | Certificate of Correction for applicant's error | |
| 110 | 55 | Submission of Terminal Disclaimer | |
| Other fee (Specify) | | | |
| Other fee (Specify) | | | |

SUBTOTAL (3) (\$) 180.00

SUBTOTAL (1) 0.00

SUBTOTAL (2) 0.00

SUBTOTAL (3) 180.00

TOTAL (\$) 180.00

CORRESPONDENCE ADDRESS

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Fax No.: (617) 248-7100

SIGNATURE BLOCK

Respectfully submitted,

Natasha C. Us

Date: August 13, 2003
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Attorney for the Applicant
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High Street Tower-125 High Street
Boston, MA 02110



2813
\$

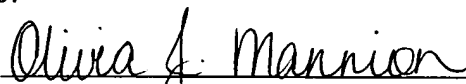
PATENT
Attorney Docket No. ASC-023DVC2

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

APPLICANT(S): Fitzgerald
SERIAL NO.: 10/022,689 GROUP NO.: 2813
FILING DATE: December 17, 2001 EXAMINER: Laura M. Schillinger
TITLE: CONTROLLING THREADING DISLOCATION DENSITIES IN GE
ON SI USING GRADED GESI LAYERS AND PLANARIZATION

CERTIFICATE OF FIRST CLASS MAILING UNDER 37 C.F.R. 1.8

I hereby certify that this correspondence, and any document(s) referred to as enclosed herein, is/are being deposited with the United States Postal Service as first class mail, postage prepaid, in an envelope addressed to the Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450 on this 13th day of August, 2003.


Olivia J. Mannion

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

Submitted herewith are: Transmittal Form (1 page); Fee Transmittal (1 page);
Supplemental Information Disclosure Statement (3 pages); Form PTO-1449 (12 pages);
References Labeled A1 to A116, B1 to B39 and C1 to C94; Check in the Amount of \$180.00;
and a return receipt postcard.

VER 9/00
2668623-1



PATENT
Attorney Docket No. ASC-023DVC2

#17 / SUPP
FDS
11-20-03
Rabala

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

APPLICANTS: Fitzgerald
SERIAL NO.: 10/022,689 GROUP NO.: 2813
FILING DATE: December 17, 2001 EXAMINER: Laura M. Schillinger
TITLE: CONTROLLING THREADING DISLOCATION DENSITIES IN GE
ON SI USING GRADED GESI LAYERS AND PLANARIZATION

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

Sir:

In accordance with the provisions of 37 C.F.R. 1.97 and 1.98, Applicants hereby make of record the patents and publications listed on the accompanying Form PTO-1449, and other information contained herein, for consideration by the Examiner in connection with the examination of the above-identified patent application. Copies of the patents and publications are enclosed.

08/20/2003 DTESSEM1 00000134 10022689

01 FC:1806

180.00 0P

REMARKS

In accordance with the provisions of 37 C.F.R. 1.97, this statement is being filed (CHECK ONE):

- ☐ (1) within three (3) months of the **filing date** of a national application other than a continued prosecution application under 37 C.F.R. 1.53(d), or within three (3) months of the **date of entry of the national stage** as set forth in 37 C.F.R. 1.491 in an international application, or before the mailing of the **first Office action** on the merits, or before the mailing of a **first Office action** after the filing of a request for continued examination under 37 C.F.R. 1.114; or
- ☒ (2) after the period defined in (1) but before the mailing date of a **final action** or a **notice of allowance** under 37 C.F.R. 1.311, and
- ☐ the requisite Statement is below, **OR**
- ☒ the requisite fee under 37 C.F.R. 1.17(p), namely **\$180.00**, is included herein, or

- ☐ (3) after the mailing date of a **final action** or **notice of allowance** but before the payment of the **issue fee**, **AND**
- ☐ the requisite Statement is below, **AND**
- ☐ the requisite petition fee under 37 C.F.R. 1.17(p), namely **\$180.00** is included herein.

In addition, Applicant wishes to inform the Examiner about the following co-pending patent applications, publications, issued patents, and Office Actions issued therein:

U.S. Serial No. 10/264,935, filed on October 4, 2002, by Lochtefeld et al.;

U.S. Serial No. 10/456,708, filed on 06/06/2003, by Lochtefeld et al.;

U.S. Serial No. 10/456,103, filed on 06/06/2003, by Lochtefeld et al.;

U.S. Publication No. 2003-0102498-A1, published 06/05/2003, by Braithwaite et al.;

U.S. Serial No. 10/389,003, filed 03/14/2003, by Fitzgerald;

U.S. Patent No. 6,107,653, issued 08/22/2000, by Fitzgerald;

U.S. Patent No. 6,291,321, issued 09/18/2001, by Fitzgerald;

U.S. Serial No. 09/611,024, filed 07/06/2000, by Fitzgerald;

U.S. Patent No. 6,573,126, issued 06/03/2003, by Cheng et al.;

U.S. Serial No. 10/384,160, filed 03/07/2003, by Cheng et al.;

U.S. Serial No. 10/379,355, filed 03/04/2003, by Cheng et al.;

U.S. Patent No. 6,602,613, issued 08/05/2003, by Fitzgerald;

U.S. Serial No. 10/391,086, filed on 03/18/2003, by Fitzgerald;

U.S. Serial No. 09/764,177, filed on 01/07/2001, by Fitzgerald;

U.S. Publication No. 2002-0100942 A1, published 08/01/2002, by Fitzgerald et al.;

U.S. Publication No. 2002-0125471, published 09/12/2002, by Fitzgerald et al.;

U.S. Publication No. 2003-0034529, published 02/20/2003, by Fitzgerald et al.;

U.S. Serial No. 10/625,018, filed 07/23/2003, by Fitzgerald et al.;

U.S. Publication No. 2002-0123197, published 07/05/2002, by Fitzgerald et al.;

U.S. Serial No. 10/611,739, filed 07/01/2003, by Fitzgerald et al.;

U.S. Publication No. 2002-0125497, published 09/12/2002, by Fitzgerald;

U.S. Serial No. 09/906,545, filed on 07/16/2001, by Fitzgerald;

U.S. Serial No. 09/906,200, filed 07/16/2001, by Fitzgerald; and

U.S. Publication No. 2003-0077867, published 07/24/2003, by Fitzgerald.


It is respectfully requested that each of the patents and publications listed on the attached Form PTO-1449, and other information contained herein, be made of record in this application.

Respectfully submitted,

Date: August 13, 2003
Reg. No. 44,381

Tel. No.: (617) 310-8327
Fax No.: (617) 248-7100

VER 12/00
2668576-1



Natasha C. Us
Attorney for the Applicant
Testa, Hurwitz, & Thibault, LLP
High Street Tower
125 High Street
Boston, Massachusetts 02110

FORM PTO - 1449

SUPPLEMENTAL INFORMATION
DISCLOSURE STATEMENT

ATTY DOCKET NO.: ASC-023DVC2

APPLICANTS: Fitzgerald

SERIAL NO.: 10/022,689

FILING DATE: December 17, 2001

GROUP: 2813



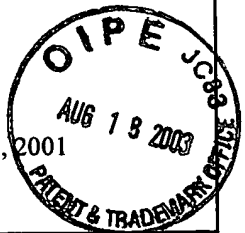
U.S. PATENT DOCUMENTS

| EXAM. INIT. | | DOCUMENT NUMBER | DATE | NAME | CLASS | SUB CLASS | FILING DATE IF APPROPRIATE |
|----------------|-----|--------------------|------------|--------------------------|-------|--------------|-------------------------------|
| | A1 | 4,010,045 | 03/01/1977 | Ruehrwein | | | |
| | A2 | 4,710,788 | 12/01/1987 | Dambkes et al. | | | |
| | A3 | 4,987,462 | 01/22/1991 | Kim et al. | | | |
| | A4 | 4,990,979 | 02/05/1991 | Otto | | | |
| | A5 | 5,013,681 | 05/07/1991 | Godbey et al. | | | |
| | A6 | 5,155,571 | 10/13/1992 | Wang et al. | | | |
| | A7 | 5,166,084 | 11/24/1992 | Pfiester | | | |
| | A8 | 5,202,284 | 04/01/1993 | Kamins et al. | | | |
| | A9 | 5,207,864 | 05/04/1993 | Bhat et al. | | | |
| | A10 | 5,208,182 | 05/04/1993 | Narayan et al. | | | |
| | A11 | 5,212,110 | 05/18/1993 | Pfiester et al. | | | |
| | A12 | 5,221,413 | 06/22/1993 | Brasen et al. | | | |
| | A13 | 5,241,197 | 08/31/1993 | Murakami et al. | | | |
| | A14 | 5,285,086 | 02/08/1994 | Fitzgerald, Jr. | | | |
| | A15 | 5,291,439 | 03/01/1994 | Kauffmann, et al. | | | |
| | A16 | 5,310,451 | 05/10/1994 | Tejwani et al. | | | |
| | A17 | 5,316,958 | 05/31/1994 | Meyerson | | | |
| | A18 | 5,346,848 | 09/13/1994 | Gruppen-Shemansky et al. | | | |
| | A19 | 5,374,564 | 12/20/1994 | Bruel | | | |
| | A20 | 5,413,679 | 05/09/1995 | Godbey | | | |
| | A21 | 5,426,069 | 06/20/1995 | Selvakumar et al. | | | |
| | A22 | 5,426,316 | 06/20/1995 | Mohammad | | | |
| | A23 | 5,461,243 | 10/24/1995 | Ek et al. | | | |
| | A24 | 5,461,250 | 10/24/1995 | Burghartz et al. | | | |
| | A25 | 5,462,883 | 10/31/1995 | Dennard et al. | | | |
| | A26 | 5,476,813 | 12/19/1995 | Naruse | | | |
| | A27 | 5,479,033 | 12/26/1995 | Baca et al. | | | |
| | A28 | 5,484,664 | 01/16/1996 | Kitahara et al. | | | |
| | A29 | 5,523,243 | 06/04/1996 | Mohammad | | | |
| | A30 | 5,523,592 | 06/04/1996 | Nakagawa et al. | | | |

EXAMINER

DATE CONSIDERED

| | | | | | | | |
|--|--|--|--|--|--|--|--|
| FORM PTO - 1449 SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT | | | | ATTY DOCKET NO.: ASC-023DVC2 APPLICANTS: Fitzgerald SERIAL NO.: 10/022,689 FILING DATE: December 17, 2001 GROUP: 2813 | | | |
|--|--|--|--|--|--|--|--|



| U.S. PATENT DOCUMENTS | | | | | | | |
|-----------------------|-----|--------------------|------------|-----------------|-------|--------------|-------------------------------|
| EXAM. INIT. | | DOCUMENT NUMBER | DATE | NAME | CLASS | SUB CLASS | FILING DATE IF APPROPRIATE |
| | A31 | 5,536,361 | 07/16/1996 | Kondo et al. | | | |
| | A32 | 5,540,785 | 07/30/1996 | Dennard et al. | | | |
| | A33 | 5,596,527 | 01/12/1997 | Tomioka, et al. | | | |
| | A34 | 5,617,351 | 04/01/1997 | Bertin, et al. | | | |
| | A35 | 5,683,934 | 11/04/1997 | Candelaria | | | |
| | A36 | 5,698,869 | 12/16/1997 | Yoshimi et al. | | | |
| | A37 | 5,728,623 | 03/17/1998 | Mori | | | |
| | A38 | 5,739,567 | 04/14/1998 | Wong | | | |
| | A39 | 5,759,898 | 06/02/1998 | Ek et al. | | | |
| | A40 | 5,777,347 | 07/07/1998 | Bartelink | | | |
| | A41 | 5,786,612 | 07/28/1998 | Otani et al. | | | |
| | A42 | 5,786,614 | 07/28/1998 | Chuang, et al. | | | |
| | A43 | 5,792,679 | 08/11/1998 | Nakato | | | |
| | A44 | 5,808,344 | 09/15/1998 | Ismail et al. | | | |
| | A45 | 5,847,419 | 12/08/1998 | Imai et al. | | | |
| | A46 | 5,877,070 | 03/02/1999 | Goesele et al. | | | |
| | A47 | 5,906,708 | 05/25/1999 | Robinson et al. | | | |
| | A48 | 5,912,479 | 06/15/1999 | Mori et al. | | | |
| | A49 | 5,943,560 | 08/24/1999 | Chang et al. | | | |
| | A50 | 5,963,817 | 10/05/1999 | Chu et al. | | | |
| | A51 | 5,966,622 | 10/12/1999 | Levine et al. | | | |
| | A52 | 5,998,807 | 12/07/1999 | Lustig et al. | | | |
| | A53 | 6,013,134 | 01/11/2000 | Chu et al. | | | |
| | A54 | 6,033,974 | 03/07/2000 | Henley et al. | | | |
| | A55 | 6,033,995 | 03/07/2000 | Muller | | | |
| | A56 | 6,058,044 | 05/02/2000 | Sugiura et al. | | | |
| | A57 | 6,074,919 | 06/13/2000 | Gardner et al. | | | |
| | A58 | 6,096,590 | 08/01/2000 | Chan et al. | | | |
| | A59 | 6,103,559 | 08/15/2000 | Gardner et al. | | | |
| | A60 | 6,111,267 | 08/29/2000 | Fischer et al. | | | |

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|-----------------|------------------------|
| EXAMINER | DATE CONSIDERED |
|-----------------|------------------------|

FORM PTO - 1449**SUPPLEMENTAL INFORMATION
DISCLOSURE STATEMENT**

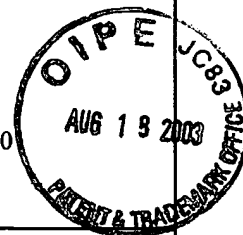
ATTY DOCKET NO.: ASC-023DVC2

APPLICANTS: Fitzgerald

SERIAL NO.: 10/022,689

FILING DATE: December 17, 2000

GROUP: 2813

**U.S. PATENT DOCUMENTS**

| EXAM. INIT. | | DOCUMENT NUMBER | DATE | NAME | CLASS | SUB CLASS | FILING DATE IF APPROPRIATE |
|----------------|-----|--------------------|------------|---------------------|-------|--------------|-------------------------------|
| | A61 | 6,117,750 | 09/12/2000 | Bensahel et al. | | | |
| | A62 | 6,130,453 | 10/10/2000 | Mei, et al. | | | |
| | A63 | 6,133,799 | 10/17/2000 | Favors, Jr., et al. | | | |
| | A64 | 6,140,687 | 10/31/2000 | Shimomura et al. | | | |
| | A65 | 6,143,636 | 11/07/2000 | Forbes, et al. | | | |
| | A66 | 6,153,495 | 11/28/2000 | Kub et al. | | | |
| | A67 | 6,154,475 | 11/28/2000 | Soref et al. | | | |
| | A68 | 6,160,303 | 12/12/2000 | Fattaruso | | | |
| | A69 | 6,162,688 | 12/19/2000 | Gardner et al. | | | |
| | A70 | 6,184,111 | 02/06/2001 | Henley et al. | | | |
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| | A73 | 6,194,722 | 02/27/2001 | Fiorini et al. | | | |
| | A74 | 6,204,529 | 03/20/2001 | Lung, et al. | | | |
| | A75 | 6,207,977 | 03/01/2001 | Augusto | | | |
| | A76 | 6,210,988 | 04/03/2001 | Howe et al. | | | |
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| | A79 | 6,235,567 | 05/22/2001 | Huang | | | |
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| | A81 | 6,249,022 | 06/19/2001 | Lin, et al. | | | |
| | A82 | 6,251,755 | 06/26/2001 | Furukawa et al. | | | |
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| | A84 | 6,266,278 | 07/24/2001 | Harari, et al. | | | |
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| | A87 | 6,313,016 | 11/06/2001 | Kibbel et al. | | | |
| | A88 | 6,316,301 | 11/13/2001 | Kant | | | |
| | A89 | 6,323,108 | 11/27/2001 | Kub et al. | | | |
| | A90 | 6,329,063 | 12/11/2001 | Lo et al. | | | |

EXAMINER**DATE CONSIDERED**

FORM PTO - 1449

SUPPLEMENTAL INFORMATION
DISCLOSURE STATEMENT

ATTY DOCKET NO.: ASC-023DVC2

APPLICANTS: Fitzgerald

SERIAL NO.: 10/022,689

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GROUP: 2813



U.S. PATENT DOCUMENTS

| EXAM. INIT. | | DOCUMENT NUMBER | DATE | NAME | CLASS | SUB CLASS | FILING DATE IF APPROPRIATE |
|----------------|------|--------------------|------------|-------------------|-------|--------------|-------------------------------|
| | A91 | 6,335,546 | 01/01/2002 | Tsuda et al. | | | 07/30/1999 |
| | A92 | 6,339,232 | 01/15/2002 | Takagi | | | 09/20/1999 |
| | A93 | 6,368,733 | 04/09/2002 | Nishinaga | | | 08/05/1999 |
| | A94 | 6,372,356 | 04/16/2002 | Thornton et al. | | | 04/028/2000 |
| | A95 | 6,399,970 | 06/04/2002 | Kubo et al. | | | 09/16/1997 |
| | A96 | 6,407,406 | 06/18/2002 | Tezuka | | | 06/29/1999 |
| | A97 | 6,425,951 | 07/30/2002 | Chu et al. | | | 08/06/1999 |
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| | A99 | 6,420,937 | 07/16/2002 | Akatsuka et al. | | | 06/14/2001 |
| | A100 | 6,521,041 | 02/18/2003 | Wu et al. | | | 04/09/1999 |
| | A101 | 6,555,839 | 04/29/2003 | Fitzgerald | | | 05/16/2001 |
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| | A103 | 6,521,041 | 02/18/2003 | Wu et al. | | | 04/09/1999 |
| | A104 | 2001/0003364 | 06/14/2001 | Sugawara et al. | | | 12/08/2000 |
| | A105 | 2002/0043660 | 04/18/2002 | Yamazaki et al. | | | 06/25/2001 |
| | A106 | 6,593,191 | 07/15/2003 | Fitzgerald | | | 05/16/2001 |
| | A107 | 6,573,126 | 06/03/2003 | Cheng et al. | | | 08/10/2001 |
| | A108 | 2002/0096717 | 07/25/2002 | Chu et al. | | | 01/25/2001 |
| | A109 | 2002/0100942 | 08/01/2001 | Fitzgerald et al. | | | 06/19/2001 |
| | A110 | 2002/0123167 | 09/05/2002 | Fitzgerald | | | 07/16/2001 |
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| | A113 | 2002/0125471 | 09/12/2002 | Fitzgerald et al. | | | 12/04/2001 |
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| | A115 | 6,603,156 | 08/05/2003 | Rim | | | 03/31/2001 |
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SUPPLEMENTAL INFORMATION
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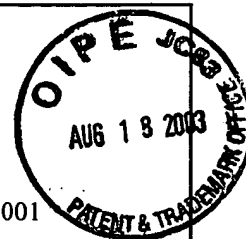
ATTY DOCKET NO.: ASC-023DVC2

APPLICANTS: Fitzgerald

SERIAL NO.: 10/022,689

FILING DATE: December 17, 2001

GROUP: 2813



FOREIGN PATENT DOCUMENTS

| EXAM. INIT. | | DOCUMENT NUMBER | DATE | COUNTRY CODE | CLASS | SUB CLASS | FILING DATE | ABSTRACT ONLY | ENGLISH LANG (Y/N) |
|----------------|-----|--------------------|------------|-----------------|-------|--------------|----------------|------------------|-----------------------|
| | B1 | 41 01 167 | 07/23/1992 | DE | | | | NO | NO |
| | B2 | 0 587 520 | 03/16/1994 | EP | | | | NO | YES |
| | B3 | 0 683 522 | 11/22/1995 | EP | | | | NO | YES |
| | B4 | 0 828 296 | 03/11/1998 | EP | | | | NO | YES |
| | B5 | 0 829 908 | 03/18/1998 | EP | | | | NO | YES |
| | B6 | 0 838 858 | 04/29/1998 | EP | | | | NO | NO |
| | B7 | 1 020 900 | 07/19/2000 | EP | | | | NO | YES |
| | B8 | 1 174 928 | 01/23/2002 | EP | | | | NO | YES |
| | B9 | 2 342 777 | 04/19/2000 | GB | | | | YES | YES |
| | B10 | 10-270685 | 10/09/1998 | JP | | | | NO | YES |
| | B11 | 11-233744 | 08/27/1999 | JP | | | | NO | NO |
| | B12 | 2000-021783 | 08/31/2000 | JP | | | | NO | YES |
| | B13 | 2000-031491 | 01/28/2000 | JP | | | | NO | NO |
| | B14 | 2001-319935 | 11/16/2001 | JP | | | | NO | YES |
| | B15 | 2002-076334 | 03/15/2002 | JP | | | | NO | YES |
| | B16 | 2002-164520 | 06/07/2002 | JP | | | | NO | YES |
| | B17 | 2002-289533 | 10/04/2002 | JP | | | | NO | YES |
| | B18 | 4-307974 | 10/30/1992 | JP | | | | NO | NO |
| | B19 | 5-166724 | 07/02/1993 | JP | | | | NO | Abstract Only |
| | B20 | 6-177046 | 06/24/1994 | JP | | | | NO | Abstract Only |
| | B21 | 7-106446 | 04/21/1995 | JP | | | | NO | NO |
| | B22 | 7-240372 | 09/12/1995 | JP | | | | NO | Abstract Only |
| | B23 | 00/48239 | 08/17/2000 | WO | | | | NO | YES |
| | B24 | 00/54338 | 09/14/2000 | WO | | | | NO | YES |

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| EXAM. INIT. | | DOCUMENT NUMBER | DATE | COUNTRY CODE | CLASS | SUB CLASS | FILING DATE | ABSTRACT ONLY | ENGLISH LANG (Y/N) |
| | B25 | 01/022482 | 03/29/2001 | WO | | | | NO | YES |
| | B26 | 01/54202 | 07/26/2001 | WO | | | | NO | YES |
| | B27 | 01/93338 | 12/06/2001 | WO | | | | NO | YES |
| | B28 | 01/99169 | 12/27/2001 | WO | | | | NO | YES |
| | B29 | 02/071488 | 09/12/2002 | WO | | | | NO | YES |
| | B30 | 02/071491 | 09/12/2002 | WO | | | | NO | YES |
| | B31 | 02/071495 | 09/12/2002 | WO | | | | NO | YES |
| | B32 | 02/082514 | 10/17/2002 | WO | | | | NO | YES |
| | B33 | 02/13262 | 02/14/2002 | WO | | | | NO | YES |
| | B34 | 02/15244 | 02/21/2002 | WO | | | | NO | YES |
| | B35 | 02/27783 | 04/04/2002 | WO | | | | NO | YES |
| | B36 | 02/47168 | 06/13/2002 | WO | | | | NO | YES |
| | B37 | 98/59365 | 12/30/1998 | WO | | | | NO | YES |
| | B38 | 99/53539 | 10/21/1999 | WO | | | | NO | YES |
| | B39 | 6-252046 | 11/19/1992 | JP | | | | NO | YES |




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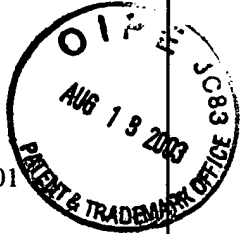
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